

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

2SA1930

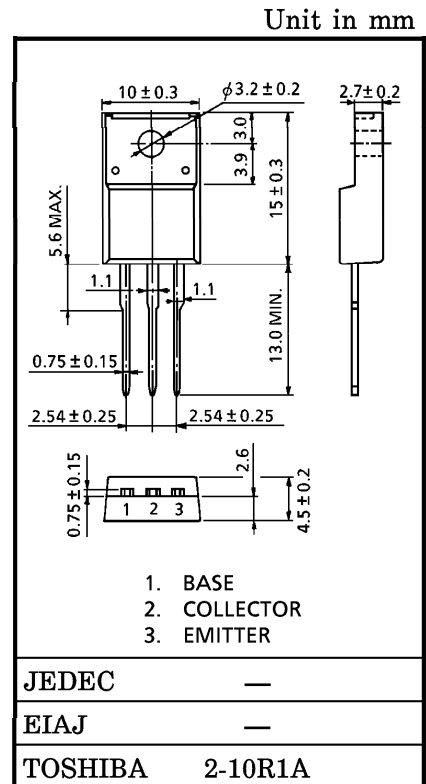
POWER AMPLIFIER APPLICATIONS

DRIVER STAGE AMPLIFIER APPLICATIONS

- High Transition Frequency : $f_T = 200$ MHz (Typ.)
- Complementary to 2SC5171

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-180	V
Collector-Emitter Voltage	V_{CE0}	-180	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-2	A
Base Current	I_B	-1	A
Collector Power Dissipation	P_C	$T_a = 25^\circ\text{C}$	2.0
		$T_c = 25^\circ\text{C}$	20
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



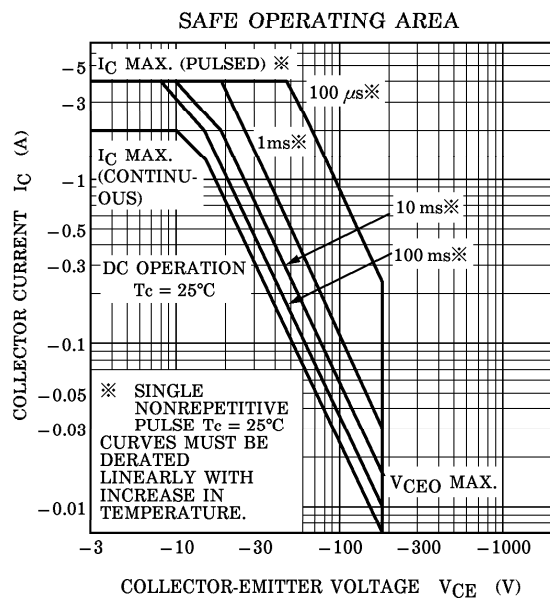
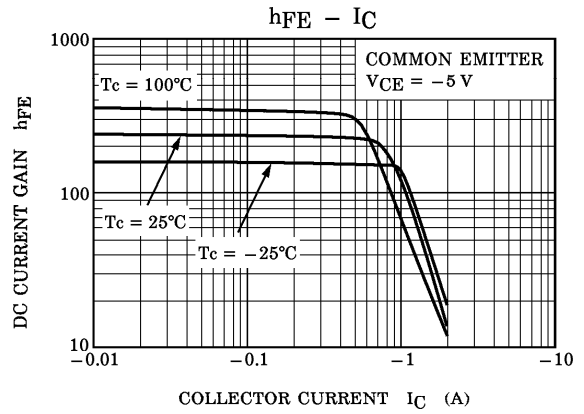
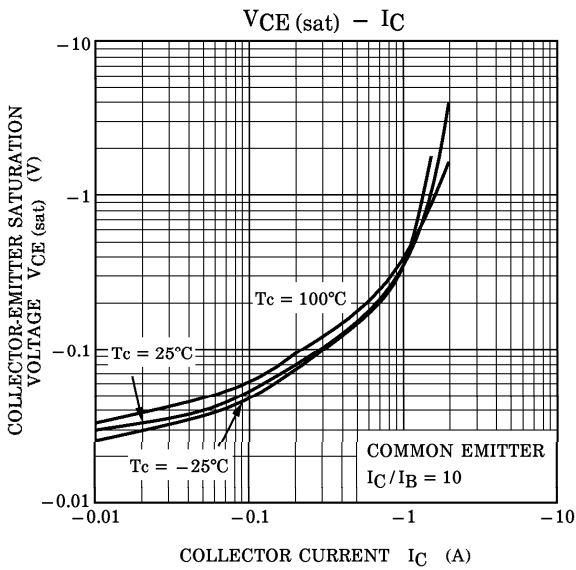
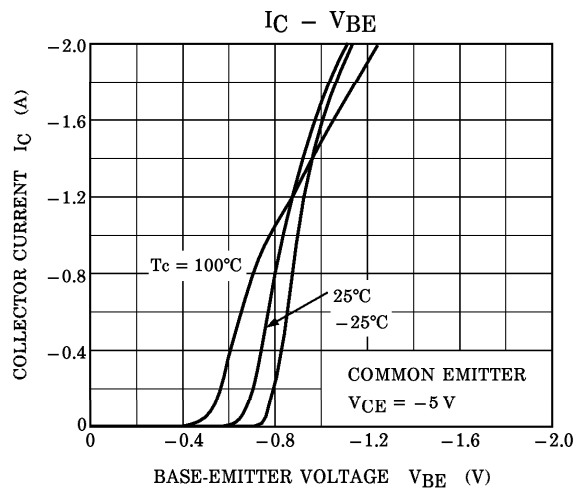
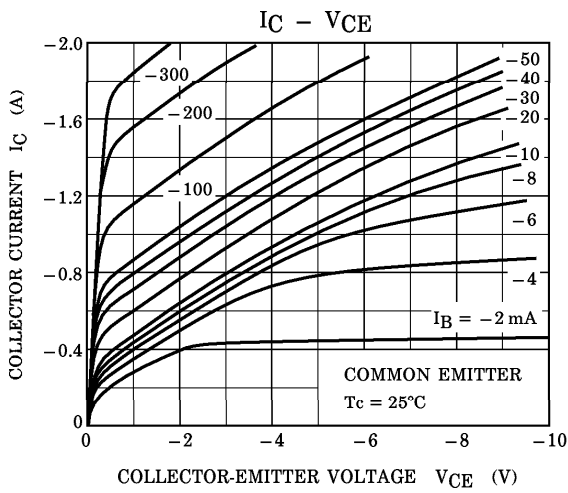
Weight : 1.7 g (Typ.)

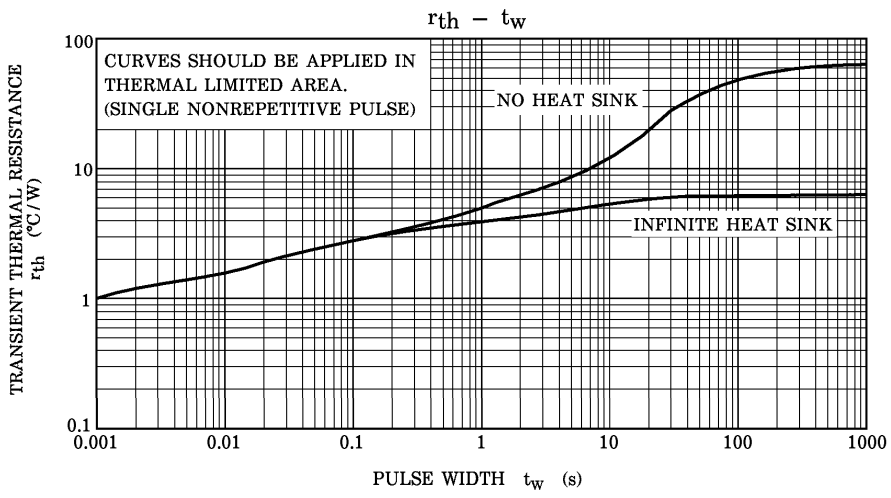
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -180$ V, $I_E = 0$	—	—	-5.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5$ V, $I_C = 0$	—	—	-5.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10$ mA, $I_B = 0$	-180	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -5$ V, $I_C = -0.1$ A	100	—	320	
	$h_{FE(2)}$	$V_{CE} = -5$ V, $I_C = -1$ A	50	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1$ A, $I_B = -0.1$ A	—	-0.24	-1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5$ V, $I_C = -1$ A	—	-0.68	-1.5	V
Transition Frequency	f_T	$V_{CE} = -5$ V, $I_C = -0.3$ A	—	200	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, $f = 1$ MHz	—	26	—	pF

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